ZnSe – Zinc Selenide

DESCRIPTIVE PROPERTIES

Structure formula:	ZnSe
Crystal structure:	cubic
Crystal axis:	(111) or (100)
Orientation:	(100); (110); (111) ±30 arc minutes. Other orientations available on request.
Production method:	Markov
Lattice parameters, Å	a = 5.6687
Specific resistivity, Ohm cm	
undoped:	1×10^{8}...1×10^{12}
doped:	5×10^{-2}...1×10^{6}
Hall mobility, $cm^2/V/sec$	400(e)
EPD, cm^{-1}	< 5×10^{3}...1×10^{5}
Density of low angle boundaries, cm^{-1}	< 2
Twins and stacking faults	twin free
Orientation accuracy:	max. 1°; typ. < 0.5°
Standard wafer sizes:	5 mm x 5 mm, 10 mm x 10 mm and round ø40 mm
Max. sizes of wafers (at thickness 1 mm):	(111) ø 55 mm (110) 45 x 20 (100) ø 51 mm
Standard thickness:	0.5 mm or 1 mm
Tolerances	
Width/Length:	± 0.050 mm
Diameter:	+ 0.000 mm / -0.100 mm
Thickness:	± 0.050 mm
Polishing:	One side or both sides polished Optical Polishing Chemical mechanical polishing

Other sizes and specifications on request.

www.princetonscientific.com
Tel. (609) 9243011 | Fax (609) 9243018 | info@princetonscientific.com | P.O. Box 148 · Easton, PA 18044